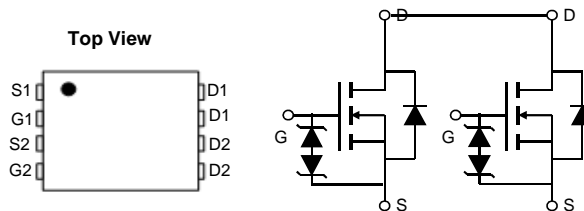


General Description

The AON7820 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{SS(ON)}$. This device is ideal for load switch and battery protection applications.

Features

| | |
|----------------------------------|----------------|
| V_{DS} | 20V |
| I_S (at $V_{GS}=4.5V$) | 35A |
| $R_{SS(ON)}$ (at $V_{GS}=4.5V$) | < 16m Ω |
| $R_{SS(ON)}$ (at $V_{GS}=3.5V$) | < 17m Ω |
| $R_{SS(ON)}$ (at $V_{GS}=2.5V$) | < 20m Ω |



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|----------------|-------------------------|------------------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Continuous Drain Current | I_S | $T_C=25^\circ\text{C}$ | 35 |
| | | $T_C=100^\circ\text{C}$ | 22 |
| Pulsed Drain Current ^C | I_{SM} | 80 | A |
| Continuous Drain Current | I_{SSM} | $T_A=25^\circ\text{C}$ | 11 |
| | | $T_A=70^\circ\text{C}$ | 9 |
| Power Dissipation ^B | P_D | $T_C=25^\circ\text{C}$ | 31 |
| | | $T_C=100^\circ\text{C}$ | 12.5 |
| Power Dissipation ^A | P_{DSM} | $T_A=25^\circ\text{C}$ | 3.1 |
| | | $T_A=70^\circ\text{C}$ | 2 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|-----|-----|---------------------------|
| Maximum Junction-to-Ambient ^A $t \leq 10\text{s}$ | $R_{\theta JA}$ | 30 | 40 | $^\circ\text{C}/\text{W}$ |
| Maximum Junction-to-Ambient ^{A D} Steady-State | | 60 | 75 | $^\circ\text{C}/\text{W}$ |
| Maximum Junction-to-Case Steady-State | $R_{\theta JC}$ | 3.2 | 4 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|---------------------------------------|--|------|------|--------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =250μA, V _{GS} =0V | 20 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =20V, V _{GS} =0V T _J =55°C | | | 1 5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} =±10V | | | 10 | μA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 0.4 | 0.7 | 1.0 | V |
| I _{D(ON)} | On state drain current | V _{GS} =4.5V, V _{DS} =5V | 80 | | | A |
| R _{SS(ON)} | Static Drain-Source On-Resistance | V _{GS} =4.5V, I _S =11A T _J =125°C | | 13 | 16 | mΩ |
| | | V _{GS} =3.5V, I _S =10A | | 13.8 | 17 | |
| | | V _{GS} =2.5V, I _S =9A | | 15.6 | 20 | mΩ |
| g _{FS} | Forward Transconductance | V _{DS} =5V, I _D =11A | | 65 | | S |
| V _{SD} | Diode Forward Voltage | I _S =1A, V _{GS} =0V | | 0.58 | 1 | V |
| I _S | Maximum Body-Diode Continuous Current | | | | 35 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =10V, f=1MHz | 1375 | 1720 | 2065 | pF |
| C _{oss} | Output Capacitance | | 215 | 312 | 410 | pF |
| C _{rss} | Reverse Transfer Capacitance | | 105 | 177 | 250 | pF |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | | 2.65 | | KΩ |
| SWITCHING PARAMETERS | | | | | | |
| Q _g | Total Gate Charge | V _{GS} =4.5V, V _{DS} =10V, I _S =11A | 14 | 18.2 | 22 | nC |
| Q _{gs} | Gate Source Charge | | | | 9.5 | nC |
| Q _{gd} | Gate Drain Charge | | | | 7.6 | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =4.5V, V _{DS} =10V, R _L =0.9Ω, R _{GEN} =3Ω | | 1.65 | | μs |
| t _r | Turn-On Rise Time | | | 3.7 | | μs |
| t _{D(off)} | Turn-Off DelayTime | | | 5.4 | | μs |
| t _f | Turn-Off Fall Time | | | 10 | | μs |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =11A, dI/dt=500A/μs | 11 | 14.5 | 18 | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =11A, dI/dt=500A/μs | 17 | 21.5 | 26 | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} t ≤ 10s value and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal impedance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

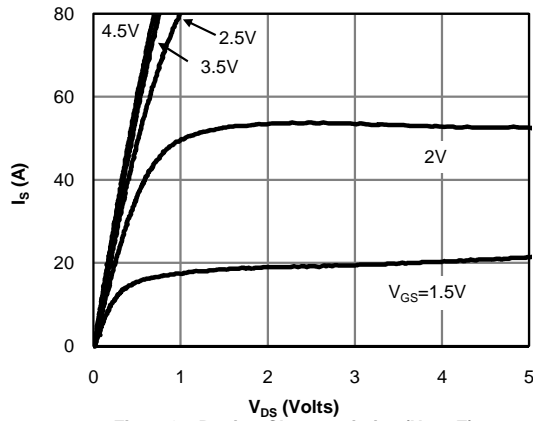


Fig 1: On-Region Characteristics (Note E)

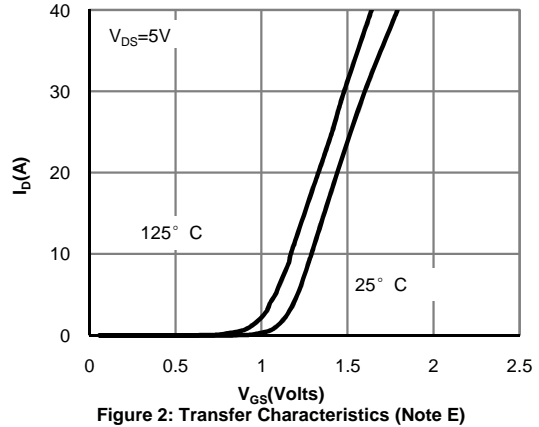


Figure 2: Transfer Characteristics (Note E)

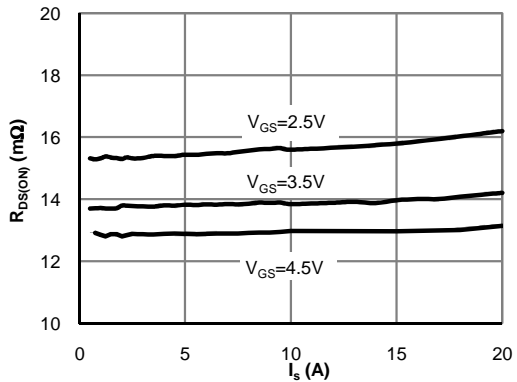


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

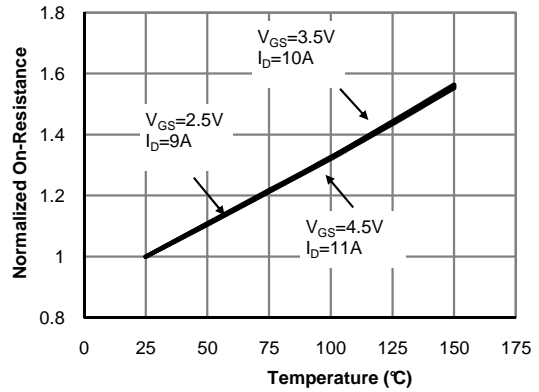


Figure 4: On-Resistance vs. Junction Temperature (Note E)

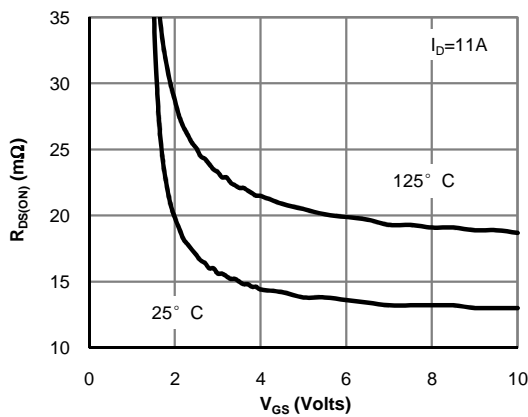


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

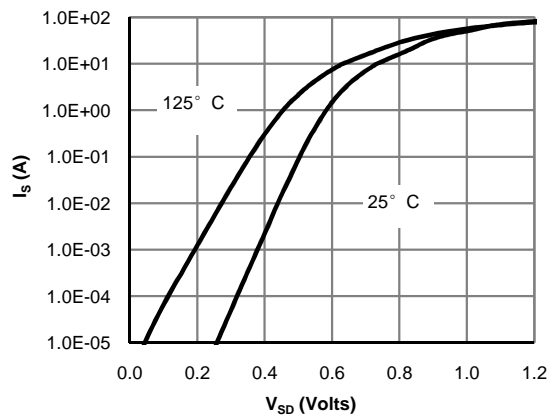


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

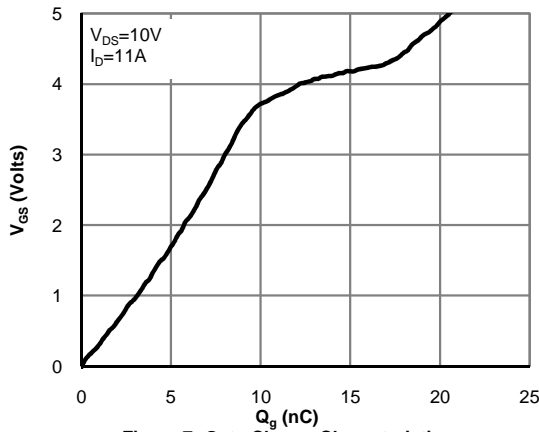


Figure 7: Gate-Charge Characteristics

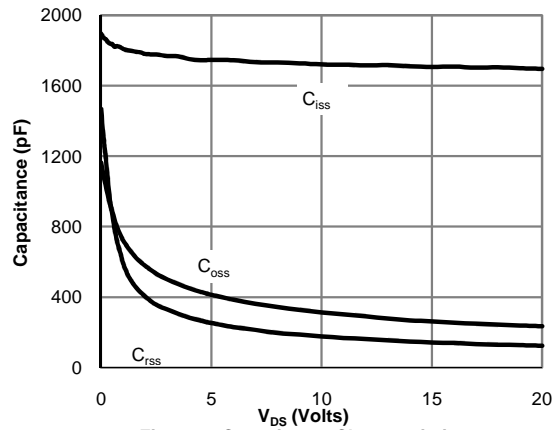


Figure 8: Capacitance Characteristics

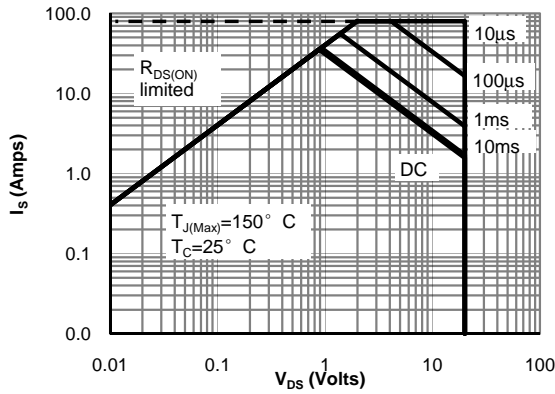


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

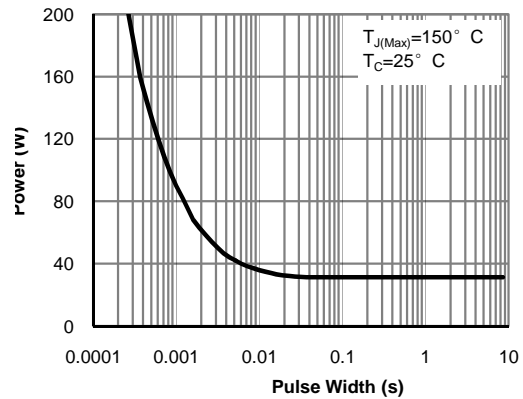


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

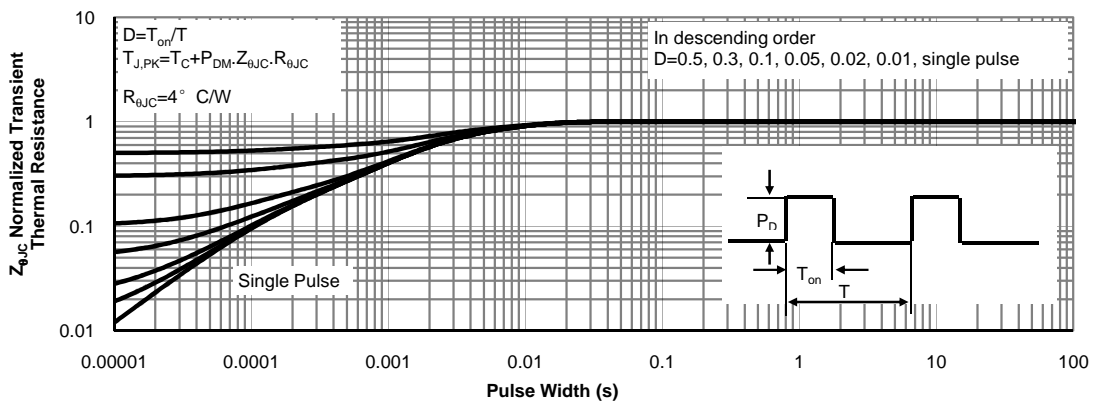


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

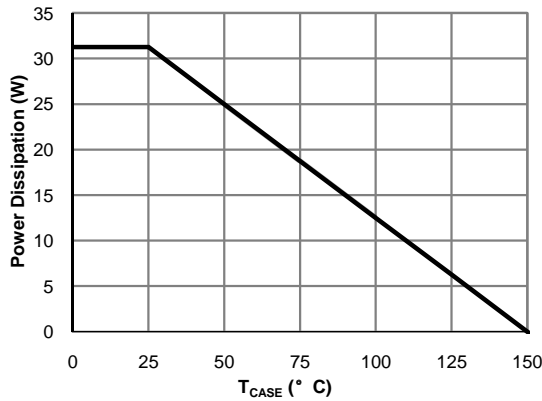


Figure 12: Power De-rating (Note F)

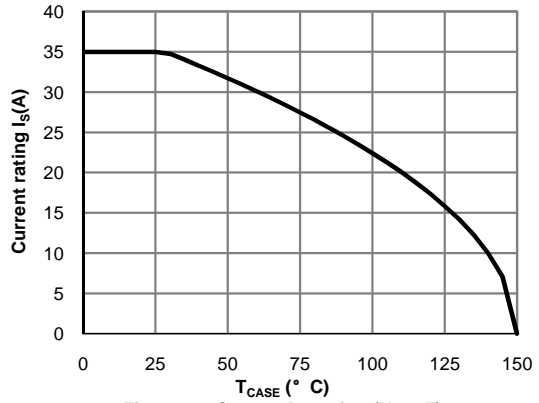


Figure 13: Current De-rating (Note F)

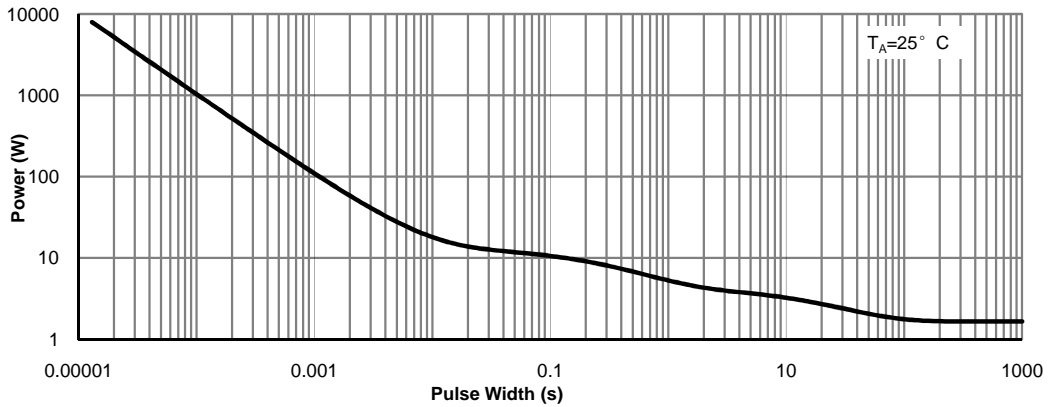


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

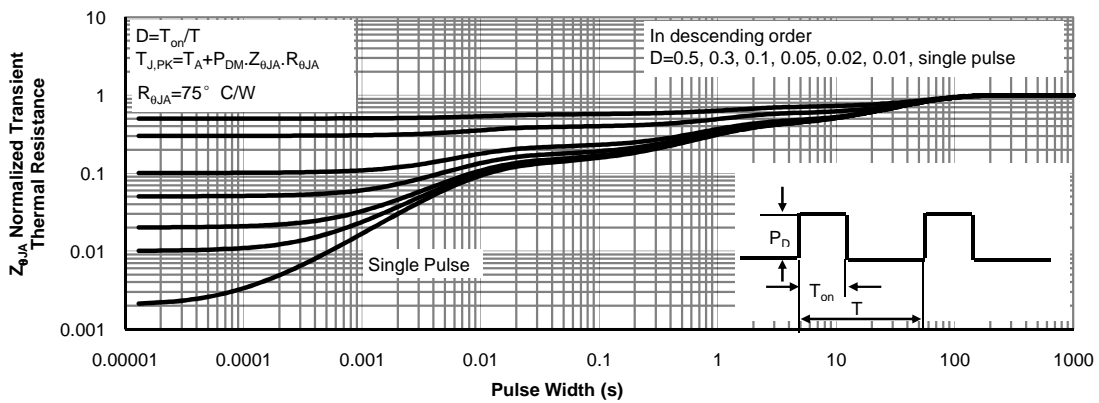
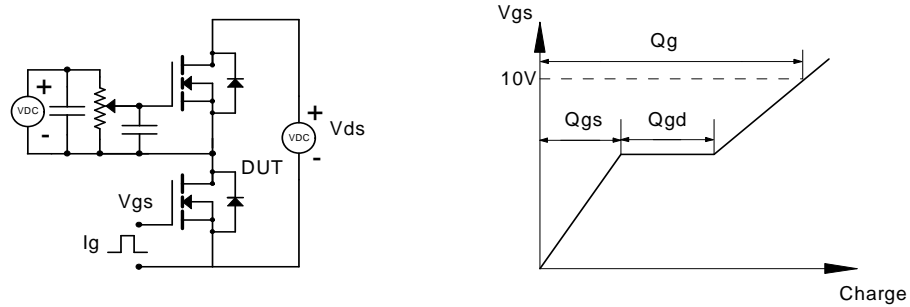
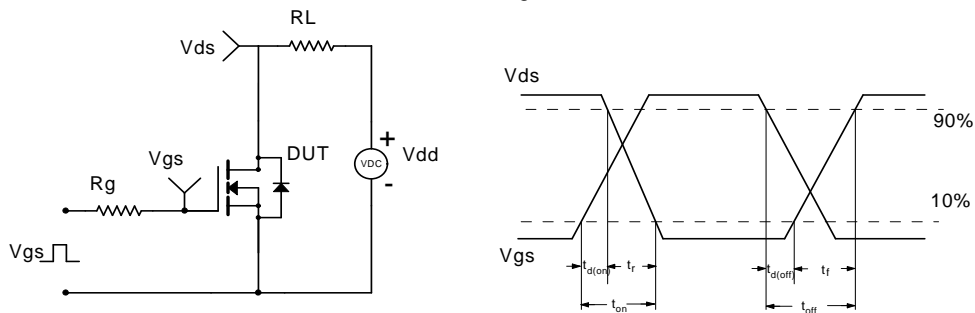


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

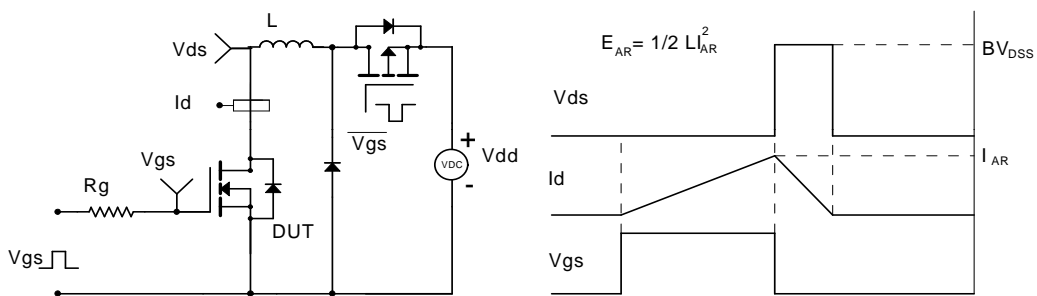
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

